

# SB30W03Z

Schottky Barrier Diode (Twin Type - Cathode Common)

## 30V, 3A Rectifier

### **Applications**

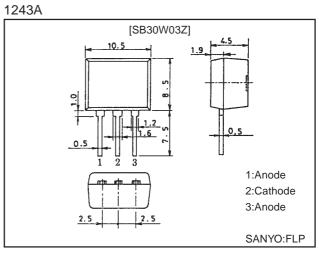
• High frequency rectification (switching regulators, converters, choppers).

#### **Features**

- · Low forward voltage ( $V_F$  max=0.55V).
- $\cdot$  Fast reverse recovery time (trr max=30ns).
- · Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

### **Package Dimensions**

unit:mm



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C (Value per element)

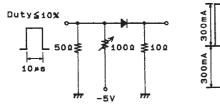
Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		30	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		35	V
Average Output Current	I0		3	А
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	20	А
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

#### **Electrical Characteristics** at Ta = 25°C (Value per element)

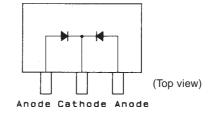
Parameter		Conditons	Ratings			Unit
	Symbol		min	typ	max	Onit
Reverse Voltage	VR	I <sub>R</sub> =1mA	30			V
Forward Voltage	٧ <sub>F</sub>	I <sub>F</sub> =3A			0.55	V
Reverse Current	IR	V <sub>R</sub> =15V			200	μA
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz		160		pF
Reverse Recovery Time	trr	I <sub>F</sub> =I <sub>R</sub> =300mA, See specified Test Circuit.			30	ns
Thermal Resistance	Rth(j-a)			70		°C/W

30mA

#### trr Test Circuit

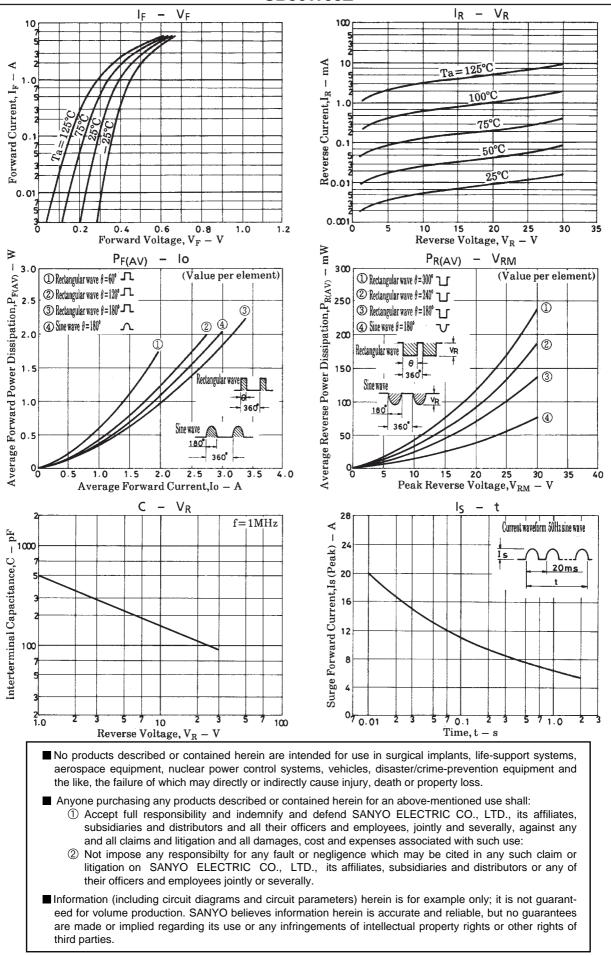


#### **Electrical Connection**



SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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This catalog provides information as of April, 1998. Specifications and information herein are subject to change without notice.